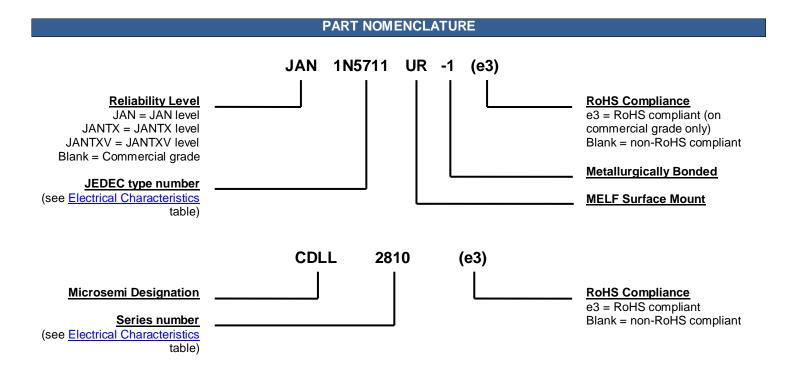
#### **MECHANICAL and PACKAGING**

- CASE: Hermetically sealed glass DO-213AA MELF (SOD-80, LL34) case package.
- TERMINALS: Tin/lead plated or RoHS compliant matte-tin (on commercial grade only) over copper clad steel. Solderable per MIL-STD-750, method 2026.
- POLARITY: Cathode end is banded.
- MOUNTING: The axial coefficient of expansion (COE) of this device is approximately +6PPM/°C. The COE of the mounting surface system should be selected to provide a suitable match with this device.
- MARKING: Part number.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: Approximately 0.2 grams.
- See <u>Package Dimensions</u> on last page.



SYMBOLS & DEFINITIONS							
Symbol	Definition						
С	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.						
f	frequency						
I <sub>R</sub>	Reverse Current: The dc current flowing from the external circuit into the cathode terminal at the specified voltage V <sub>R</sub> .						
Io	Average Rectified Output Current: The Output Current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.						
t <sub>rr</sub>	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.						
$V_{(BR)}$	Breakdown Voltage: A voltage in the breakdown region.						
V <sub>F</sub>	Forward Voltage: A positive dc anode-cathode voltage the device will exhibit at a specified forward current.						
V <sub>R</sub>	Reverse Voltage: A positive dc cathode-anode voltage below the breakdown region.						
V <sub>RWM</sub>	Working Peak Reverse Voltage: The peak voltage excluding all transient voltages (ref JESD282-B). Also sometimes known historically as PIV.						



# ELECTRICAL CHARACTERISTICS @ T<sub>A</sub> = 25 °C unless otherwise noted

TYPE NUMBER	MINIMUM BREAKDOWN VOLTAGE	MAXIMUM FORWARD VOLTAGE	MAXIMUM FORWARD VOLTAGE	WORKING PEAK REVERSE VOLTAGE	MAXIMUM REVERSE LEAKAGE CURRENT		$\label{eq:maximum} \begin{aligned} \text{MAXIMUM} \\ \text{CAPACITANCE} \\ \text{@ $V_R = 0$} \\ \text{VOLTS} \\ \text{f = 1.0 MHz} \end{aligned}$
	V <sub>(BR)</sub> @ 10 μA	V <sub>F</sub> @ 1 mA	V <sub>F</sub> @ I <sub>F</sub>	V <sub>RWM</sub>	I <sub>R</sub> @ V <sub>R</sub>		Ст
	Volts	Volts	V @ mA	V (pk)	nA	Volts	pF
1N5711UR-1	70	0.41	1.0 @ 15	50	200	50	2.0
1N5712UR-1	20	0.41	1.0 @ 35	16	150	16	2.0
1N6857UR-1	20	0.35	0.75 @ 35	16	150	16	4.5
1N6858UR-1	70	0.36	0.65 @ 15	50	200	50	4.5
CDLL2810	20	0.41	1.0 @ 35	50	100	15	2.0
CDLL5711	70	0.41	1.0 @ 15	50	200	50	2.0
CDLL5712	20	0.41	1.0 @ 35	16	150	16	2.0
CDLL6263	60	0.41	1.0 @ 15	16	200	50	2.2
CDLL6857	20	0.35	0.75 @ 35	16	150	16	4.5
CDLL6858	70	0.36	0.65 @ 15	50	200	50	4.5

### NOTE:

1. Effective minority carrier lifetime  $(\tau)$  is 100 pico seconds.



#### **GRAPHS**

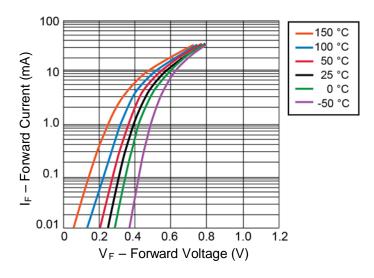


FIGURE 1

I-V Curve showing typical Forward Voltage Variation

Temperature for the 1N5712UR-1, CDLL5712 and CDLL2810 Schottky Diodes

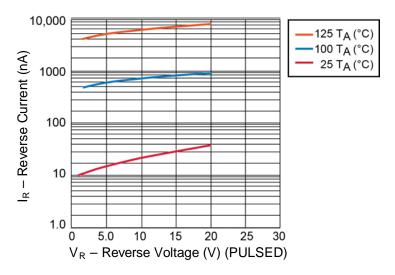


FIGURE 2

1N5712UR-1, CDLL5712 and CDLL2810 Typical variation of Reverse
Current (I<sub>R</sub>) vs Reverse Voltage (V<sub>R</sub>) at Various Temperatures



#### **GRAPHS**

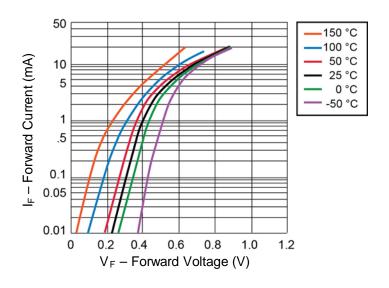
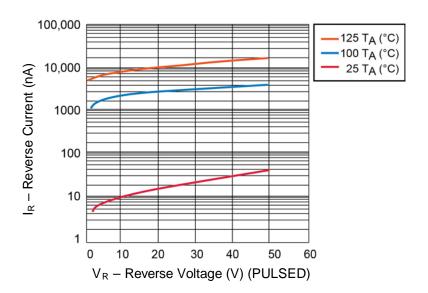


FIGURE 3

I – V curve showing typical Forward Voltage Variation
With Temperature Schottky Diode 1N5711UR-1





## **GRAPHS**

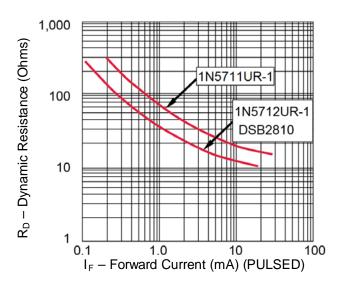


FIGURE 5

Typical Dynamic Resistance ( $R_D$ ) vs Forward Current ( $I_F$ )